

ESD9NS5V

2-Lines Bidirectional Transient Voltage Suppressors

[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

Descriptions

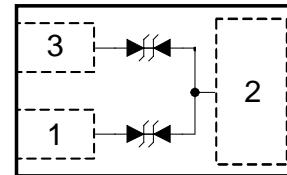
The ESD9NS5V is a transient voltage suppressors (TVS) which provide a very high level protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). It is designed to replace multilayer varistors (MLV) in consumer equipments applications such as mobile phone, notebook, PAD, STB, LCD TV etc.

The ESD9NS5V was past ESD transient voltage up to $\pm 30kV$ (contact) according to IEC61000-4-2 and withstand peak current up to 9A for 8/20us pulse according to IEC61000-4-5.

The ESD9NS5V is available in DFN1006-3L package. Standard products are Pb-free and Halogen-free.



DFN1006-3L



Pin configuration (Top view)



DFN1006-3L

S = Device code

***** = Month code (A~Z)

Marking

Features

- Working voltage : 5V
- Peak power (tp=8/20us) : 99W Max.
- Peak current (tp=8/20us) : 9A Max.
- Transient protection
IEC61000-4-2, Level 4 : $\pm 30kV$ air
: $\pm 30kV$ contact
- Low clamping voltage
- Low leakage current
- Small package

Order information

Device	Package	Shipping
ESD9NS5V-3/TR	DFN1006-3L	10000/Tape&Reel

Applications

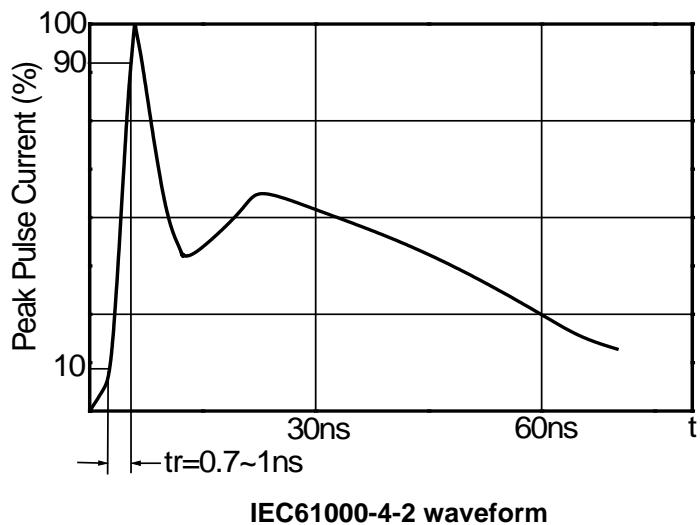
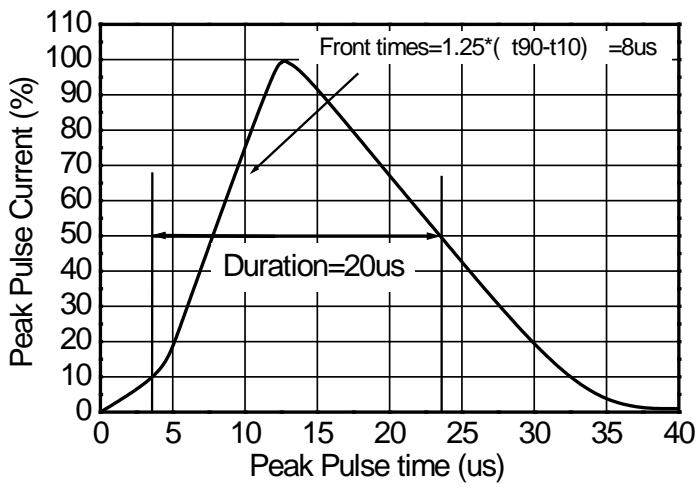
- Cell phone
- PMP
- MID
- PDA
- Digital camera
- Other electronics equipments

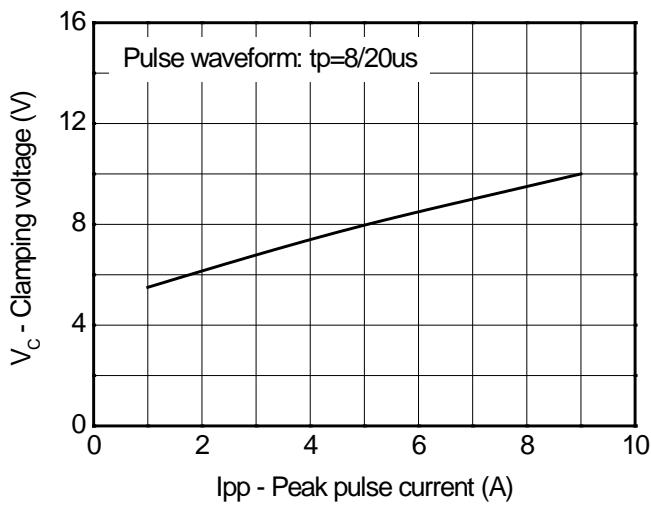
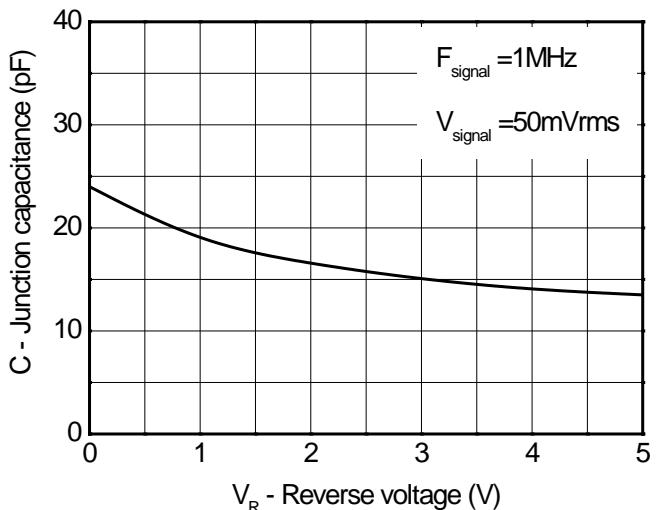
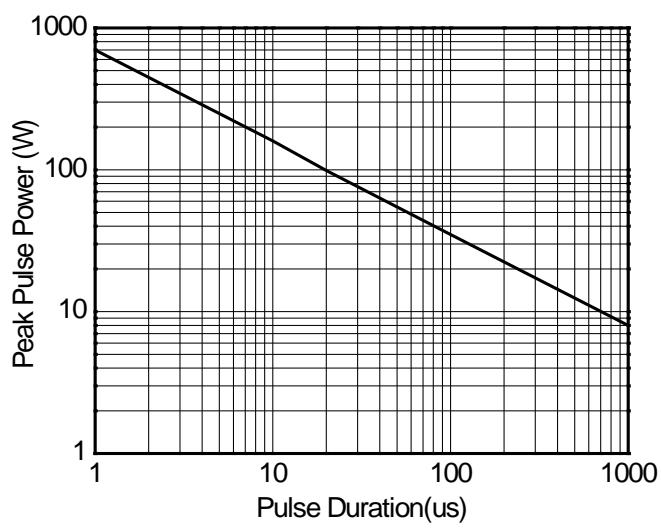
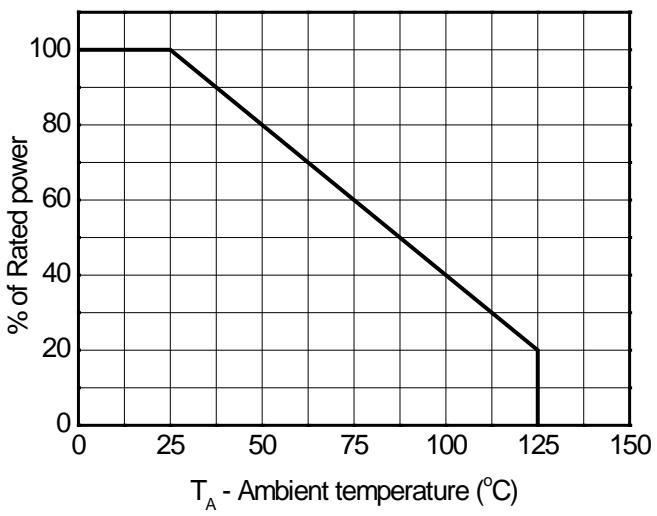
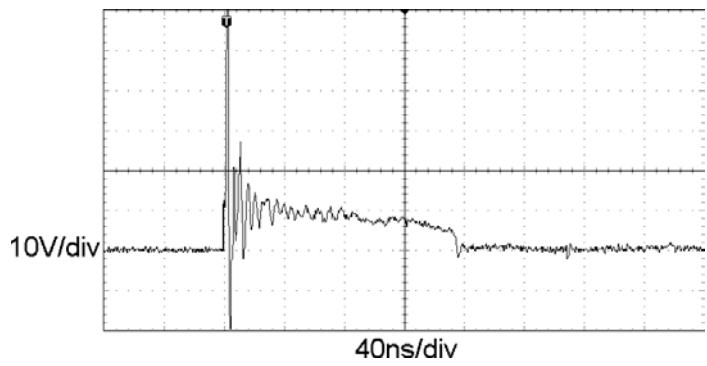
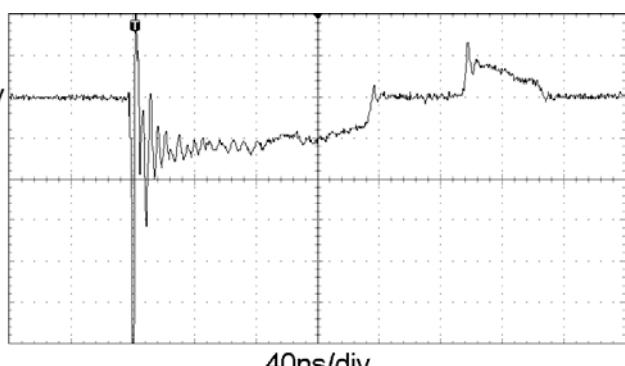
Absolute maximum ratings

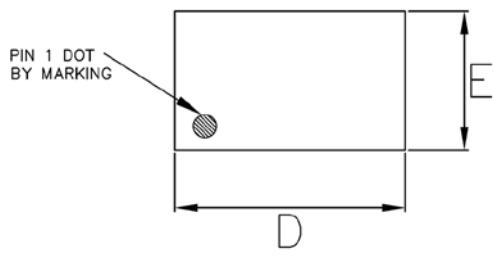
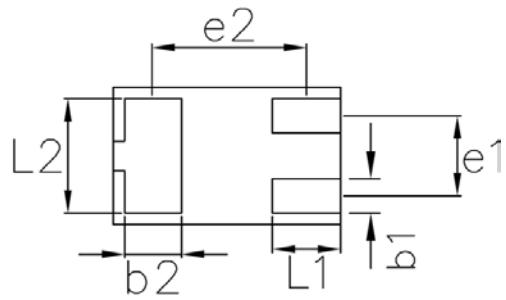
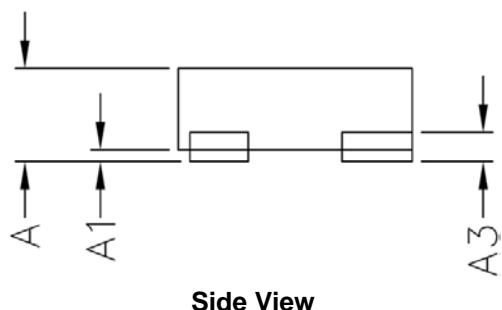
Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p=8/20\mu s$)	P _{pk}	99	W
Peak pulse current ($t_p=8/20\mu s$)	I _{pp}	9	A
ESD voltage IEC61000-4-2 air	V _{ESD}	±30	kV
ESD voltage IEC61000-4-2 contact		±30	
Junction temperature	T _J	125	°C
Operating temperature	T _{OP}	-40~85	°C
Lead temperature	T _L	260	°C
Storage temperature	T _{STG}	-55~150	°C

Electronics characteristics (Ta=25 °C, unless otherwise noted)

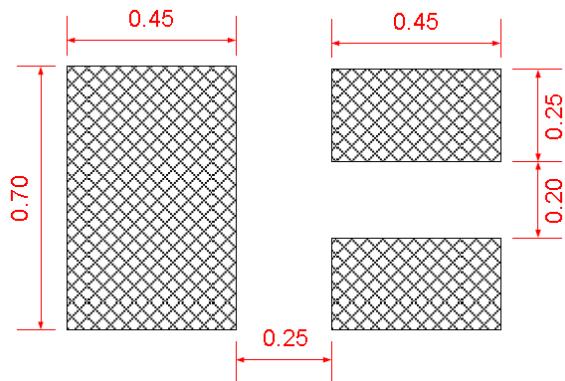
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V _{RWM}				5.0	V
Reverse leakage current	I _R	V _{RWM} =5V			1	uA
Reverse breakdown voltage	V _{BR}	I _T =1mA	5.8	6.8	8.1	V
Clamping voltage	V _C	I _{pp} =1A $t_p=8/20\mu s$			6	V
		I _{pp} =9A $t_p=8/20\mu s$			11	V
Junction capacitance	C _J	F=1MHz, V _R =0V		24	30	pF



Typical characteristics (Ta=25°C, unless otherwise noted)

Clamping voltage vs. Peak pulse current

Capacitance vs. Reveres voltage

Non-Repetitive Peak Pulse Power vs. Pulse time

Power derating vs. Temperature

**ESD clamping voltage
(IEC61000-4-2 +8kV contact)**

**ESD clamping voltage
(IEC61000-4-2 -8kV contact)**

Package outline dimensions
DFN1006-3L

Top View

Bottom View

Side View

Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	>0.40	-	0.40
A1	0.00	-	0.05
A3	0.125REF		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b1	0.10	0.15	0.20
b2	0.20	0.25	0.30
L1	0.20	0.30	0.40
L2	0.40	0.50	0.60
e1	0.35BSC		
e2	0.675BSC		

Recommend PCB Layout (Unit: mm)

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.